

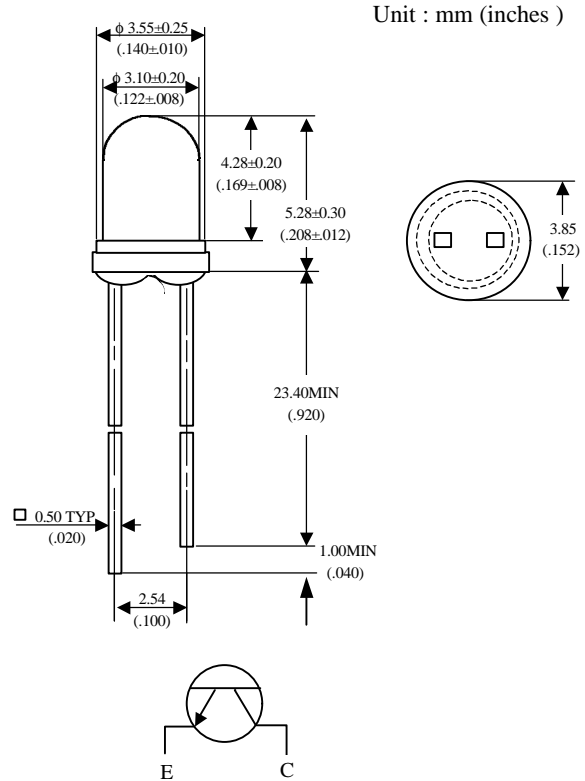
Description

The MID-32A22 is a NPN silicon phototransistor mounted in a lensed, special dark plastic package. The lensing effect of the package allows an acceptance half view angle of 20° that is measured from the optical axis to the half power point.

Features

- Wide range of collector current
- Lensed for high sensitivity
- Low cost plastic package
- Good spectral matching IRED (λ_p 940 nm) type
- Acceptance view angle : 40°

Package Dimensions



Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted .
2. Protruded resin under flange is 1.5 mm (.059") max
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A=25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Collector-Emitter Voltage	30	V
Emitter-Collector Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage	I _c =0.1mA Ee=0	V _{(BR)CEO}	30			V
Emitter-Collector Breakdown Voltage	Ie=0.1mA Ee=0	V _{(BR)ECO}	5			V
Collector-Emitter Saturation Voltage	I _c =0.5mA Ee=0.1mW/cm ²	V _{CE(SAT)}			0.4	V
Rise Time	V _{CC} =5V, R _L =1KΩ	Tr		15		μS
Fall Time	I _c =1mA	Tf		15		
Collector Dark Current	V _{CE} =10V Ee=0	I _{CEO}			100	nA
On State Collector Current	V _{CE} =5V Ee=0.1mW/cm ²	I _{C(ON)}		0.4		mA

Typical Optical-Electrical Characteristic Curves

